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Vishay Semiconductors

SOT-227 Power Module Single Switch - Power MOSFET, 400 A



PRIMARY CHARACTERISTICS					
V_{DSS}	150 V				
R _{DS(on)} at 200 A	1.93 m Ω				
I _D	300 A at 90 °C				
Type	Modules - MOSFET				
Package	SOT-227				

FEATURES

- I_D = 400 A, T_C = 25 °C
- ThunderFET Power MOSFET
- Excellent gate charge x R_{DS(on)} product (FOM)
- · Reduced switching and conduction losses
- Ultra low gate charge (Q_q)
- Maximum 175 °C junction temperature
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- DC/DC conversions
- Motor drives
- DC/AC inverter
- Power supplies
- Uninterruptible power supplies
- AC/DC switch-mode power supplies

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
MOSFET						
Drain to source voltage	V_{DSS}		150	V		
Continuous drain current, V _{GS at} 10 V		T _C = 25 °C	400			
Continuous drain current, v _{GS at} 10 v	Ι _D	T _C = 90 °C	300	Α		
Pulsed drain current	I _{DM} ⁽¹⁾		860			
Power dissipation	P_D	T _C = 25 °C	909	W		
Gate to source voltage	V _{GS}		± 20	V		
Single pulse avalanche current	E _{AS}		720	J		
Avalanche current	I _{AS}	T_C = 25 °C, L = 10 mH, V_{GS} = 10 V	120	Α		
MODULE						
Operating junction temperature range	TJ		-55 to +175	°C		
Operating storage temperature range	T _{Stg}		-40 to +150	C		
Insulation voltage (RMS)	V _{ISOL}	any terminal to case, t = 1 min	2500	V		

Note

(1) Limited at max. junction temperature



THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction tempera	ature range	TJ		-55	-	175	°C
Operating storage tempera	ture range	T _{Stg}		-40	-	150	
Junction to case	MOSFET	R _{thJC}		-	-	0.165	°C/W
Case to heatsink	Module	R _{thCS}	Flat, greased surface	-	0.1	-	C/VV
Weight				-	30	-	g
Mounting torque			Torque to terminal	-	-	1.1 (9.7)	Nm (lbf. in)
Mounting torque			Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf. in)
Case style				SOT-227			

ELECTRICAL CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Drain to source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 500 \mu\text{A}$	150	-	-	V	
Breakdown voltage temperature coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	Reference to 25 °C, I _D = 1.0 mA	-	9.0	-	mV/°C	
Static drain to source on-resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 200 A	-	1.93	2.75	mΩ	
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 1.0 \text{ mA}$	1.80	3.46	5.4	V	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_{J}$	$V_{DS} = V_{GS}, I_D = 1.0 \text{ mA}$ (25 °C to 125 °C)	-	9.6	-	mV/°C	
Forward transconductance	9 _{fs}	V _{DS} = 15 V, I _D = 100 A, V _{GS} = 10 V	-	200	-	S	
Dusin to source leakage aurent		V _{DS} = 150 V, V _{GS} = 0 V	-	0.5	10.0		
Drain to source leakage current	I _{DSS}	V _{DS} = 150 V, V _{GS} = 0 V, T _J = 150 °C	-	19	-	μA	
Gate to source leakage	I _{GSS}	$V_{GS} = \pm 20 \text{ V}$	-	-	± 200	nA	
Total gate charge	Qg	I _D = 250 A	-	250	-		
Gate to source charge	Q_{gs}	$V_{DS} = 75 \text{ V}$	-	79	-	nC	
Gate to drain ("Miller") charge	Q_{gd} $V_{GS} = 10 \text{ V}$		-	82	-		
Turn-on delay time	t _{d(on)}	V _{DD} = 75 V	-	139	-		
Rise time	t _r	VDD = 73 V		285	-]	
Turn-off delay time	$t_{d(off)}$ $R_g = 1 \Omega$		-	120	-	ns	
Fall time	t _f	V _{Ce} = 1() V		142	-		
Input capacitance	C _{iss}	V _{GS} = 0 V		13.7	-		
Output capacitance	C_{oss} $V_{DS} = 25 V$		-	2.2	-	nF	
Reverse transfer capacitance	C _{rss}	f = 1 MHz	ı	0.104	-		

SOURCE-DRAIN RATINGS AND CHARACTERISTICS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Continuous source current (body diode)	Is		-	-	476	
Pulsed source current (body diode)	I _{SM}	MOSFET symbol showing the integral reverse p-n junction diode	-	-	850	А
Diode forward voltage	V _{SD}	V _{SD} I _S = 250 A, V _{GS} = 0 V		0.95	-	V
Reverse recovery time	t _{rr}	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		171	-	ns
Reverse recovery charge	Q _{rr}			1032	-	nC
Reverse recovery current	I _{RM}			1	Α	



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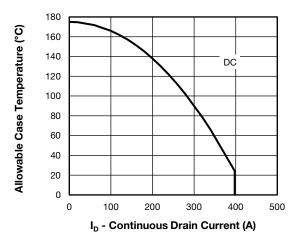


Fig. 1 - Maximum Continuous Drain Current vs. Case Temperature

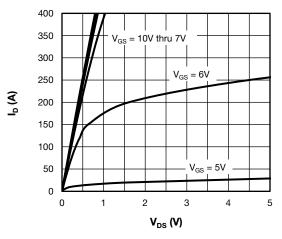


Fig. 2 - Typical Drain to Source Current Output Characteristics at $T_{\rm J} = 25~^{\circ}\text{C}$

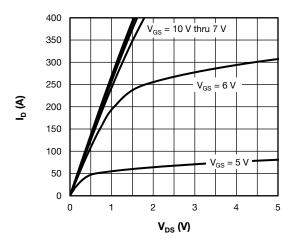


Fig. 3 - Typical Drain to Source Current Output Characteristics at $T_{J} = 125\ ^{\circ}\text{C}$

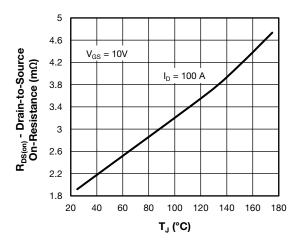


Fig. 4 - Typical Drain-to-Source On-Resistance vs. Temperature

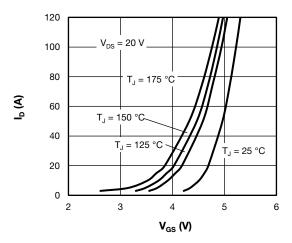


Fig. 5 - Typical Transfer Characteristics

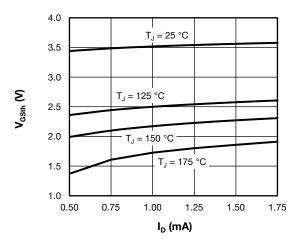


Fig. 6 - Typical Gate Threshold Voltage Characteristics



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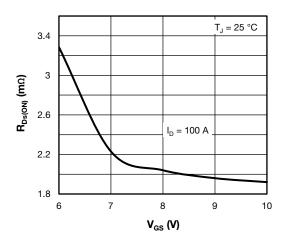


Fig. 7 - Typical Drain - State Resistance vs. Gate to Source Voltage

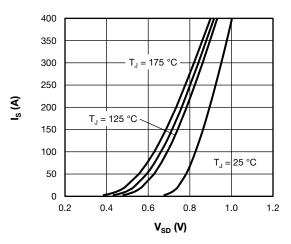


Fig. 8 - Typical Body Diode Source-to-Drain Current Characteristics

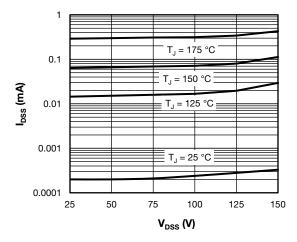


Fig. 9 - Typical Zero Gate Voltage Drain Current

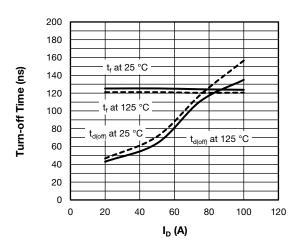


Fig. 10 - Typical Turn-off Switching Time vs. I_D

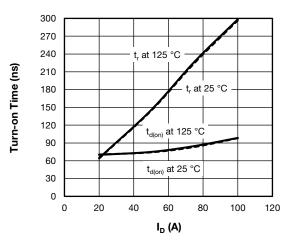


Fig. 11 - Typical Turn-on Switching Time vs. I_D

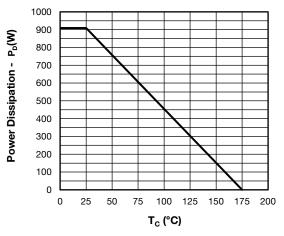


Fig. 12 - Power Dissipation Curve

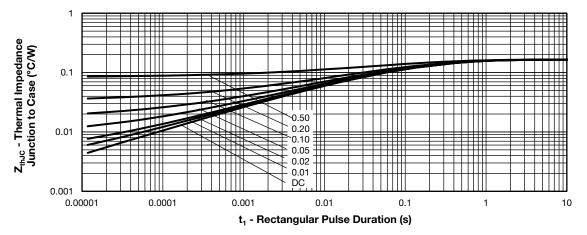


Fig. 13 - Maximum Thermal Impedance Junction-to-Case Characteristics

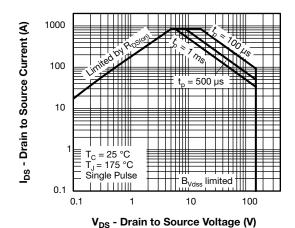
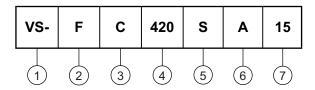


Fig. 14 - Safe Operating Area

ORDERING INFORMATION TABLE

Device code



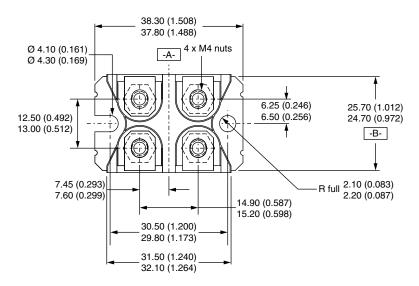
- 1 Vishay Semiconductors product
- 2 MOSFET module
- MOSFET die generation
- Current rating (420 = 420 A)
- 5 Circuit configuration (S = single switch)
- 6 Package indicator (SOT-227)
- **7** Voltage rating (15 = 150 V)

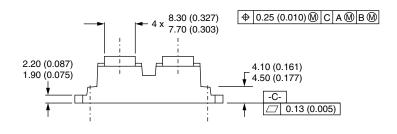


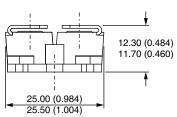
CIRCUIT CONFIGURATION				
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING		
Single switch	O	G (2) Lead Assignment (S) (D) (G) (A) (B) (C) (C) (C) (C) (C) (C) (C		



DIMENSIONS in millimeters

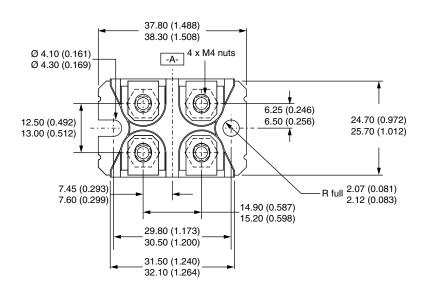


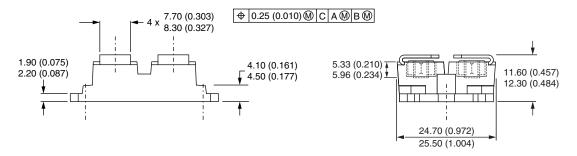




SOT-227 Generation 2

DIMENSIONS in millimeters (inches)





Note

· Controlling dimension: millimeter



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